

MH180 Hall-effect sensor is a temperature stable, stress-resistant sensor. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

MH180 includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, Pull-up resistor output. Advanced DMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

This device requires the presence of both south and north polarity magnetic fields for operation. In the presence of a south polarity field of sufficient strength, the device output sensor on, and only switches off when a north polarity field of sufficient strength is present.

MH180 is rated for operation between the ambient temperatures –40°C and 85°C for the E temperature range, and –40°C to 125°C for the K temperature range. The two package styles available provide magnetically optimized solutions for most applications. Package SO is an SOT-23, a miniature low-profile surface-mount package; Package SF is an SOT89-5L, a low-profile surface-mount package, while package UA is a three-lead ultra mini SIP for through-hole mounting.

Packages is Halogen Free standard and which have been verified by third party lab.

Features and Benefits

- DMOS Hall IC Technology.
- Reverse bias protection on power supply pin.
- Chopper stabilized amplifier stage.
- Optimized for BLDC motor applications.
- Reliable and low shifting on high Temp condition.
- Switching offset compensation at typically 69 kHz.
- Good ESD Protection.
- 100% tested at 125 °C for K.
- Custom sensitivity / Temperature selection are available.
- RoHS compliant 2011/65/EU and Halogen Free

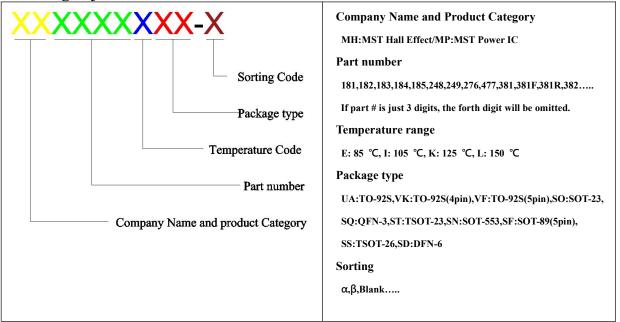
Applications

- High temperature Fan motor
- 3 phase BLDC motor application
- Speed sensing
- Position sensing
- Current sensing
- Revolution counting
- Solid-State Switch
- Linear Position Detection
- Angular Position Detection
- Proximity Detection
- High ESD Capability

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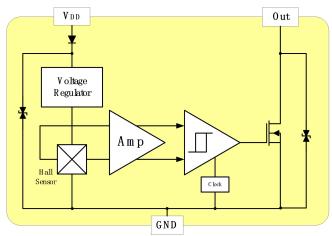
Ordering Information



Part No.	Temperature Suffix	Package Type
MH180KUA	$K (-40^{\circ}C \text{ to} + 125^{\circ}C)$	UA (TO-92S)
MH180KSO	$K (-40^{\circ}C \text{ to} + 125^{\circ}C)$	SO (SOT-23)
MH180EUA	$E (-40^{\circ}C \text{ to} + 85^{\circ}C)$	UA (TO-92S)
MH180ESO	$E \left(-40^{\circ}\text{C to} + 85^{\circ}\text{C}\right)$	SO (SOT-23)

KUA spec is using in industrial and automotive application. Special Hot Testing is utilized.

Functional Diagram





Absolute Maximum Ratings At (Ta=25°C)

Characteristics			Values	Unit
Supply voltage, (VDD)			28	V
Output Voltage,(Vout)			28	V
Reverse voltage, (V_{DD})			-28	V
Magnetic flux density			Unlimited	Gauss
Output current, (Isink)		50	mA	
On aroting Tomporature Range	(T_{α})	"E" version	-40 to +85	°C
Operating Temperature Range	s, (1a)	"K" version	-40 to +125	°C
Storage temperature range, (<i>Ts</i>)			-65 to +150	°C
Maximum Junction Temp,(<i>Tj</i>)		150	°C	
Thermal Resistance	$(heta_{ja})$	UA / SO/ SF	206 / 543/ 156	°C/W
	$(heta_{jc})$	UA / SO/ SF	148 / 410/ 34	°C/W
Package Power Dissipation, (P_D) UA / SO/ SF			606 / 230 / 800	mW

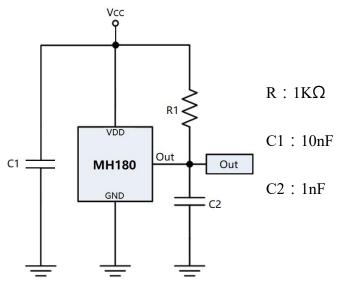
Note: Do not apply reverse voltage to V_{DD} and V_{OUT} Pin, It may be caused for Miss function or damaged device.

Electrical Specifications

DC Operating Parameters: $T_A=+25$ °C, $V_{DD}=12V$

Parameters	Test Conditions	Min	Тур	Max	Units
Supply Voltage, (V_{DD})	Operating	2.5		24.0	V
Supply Current, (I_{DD})	B <b<sub>OP</b<sub>			5.0	mA
Output Saturation Voltage, (V_{sat})	$I_{OUT} = 20 \text{ mA}, B>B_{OP}$			400.0	mV
Output Leakage Current, (Ioff)	I_{OFF} B <brp, <math="">V_{OUT}= 12V</brp,>			10.0	uA
Internal Oscillator Chopper Frequency,(fosc)			69		kHz
Output Rise Time, (T_R)	RL=1.1K Ω , CL =20pF		0.04	0.45	uS
Output Fall Time, (T_F)	RL=820Ω; CL =20pF		0.18	0.45	uS
Electro-Static Discharge	HBM	4			KV
Operate Point,(BOP)	UA, SF, SO	10	50	90	Gauss
Release Point,(BRP)	UA, SF, SO	90	-50	-10	Gauss
Hysteresis,(BHYS)			100		Gauss

Typical application circuit



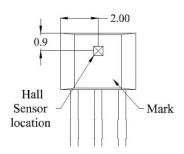


Sensor Location, Package Dimension and Marking

UA Package

4.10 3.90 180 3.10 0.557 2.90 XXX 0.457 0.42 0.56 0.56 14.5 0.38 0.51 1.27 0.36

Hall Chip location

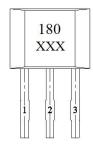


NOTES:

- 1. Controlling dimension: mm
- Leads must be free of flash and plating voids
- 3. Do not bend leads within 1 mm of lead to package interface.
- 4. PINOUT:

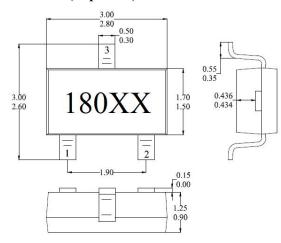
Pin 1	V_{DD}
Pin 2	GND
Pin 3	Output

Output Pin Assignment (Top view)



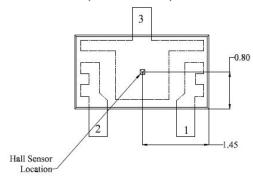
SO Package

(Top View)



Hall Plate Chip Location

(Bottom view)



NOTES:

1. PINOUT (See Top View at left:)

Pin 1 V_{DD}

Pin 2 Output

Pin 3 GND

- 2. Controlling dimension: mm
- 3. Lead thickness after solder plating will be 0.254mm maximum

(For reference only)Land Pattern

